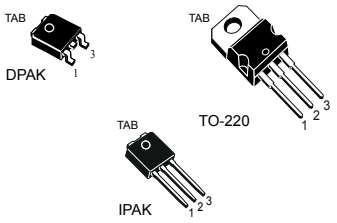
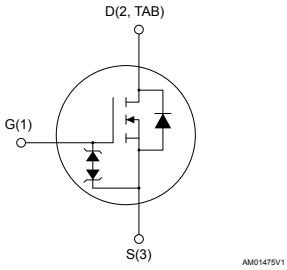
STD9N60M2, STP9N60M2, STU9N60M2

Datasheet

N-channel 600 V, 0.72 Ω typ., 5.5 A, MDmesh™ M2 Power MOSFETs in DPAK, TO-220 and IPAK packages





Features

Order codes	V_{DS} @ T_{Jmax}	$R_{DS(on)}$ max.	I_D	P_{TOT}	Package
STD9N60M2	650 V	0.78 Ω	5.5 A	60 W	DPAK
STP9N60M2					TO-220
STU9N60M2					IPAK

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the MDmesh™ M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high-efficiency converters.

STPOWER

Product status link
STD9N60M2
STP9N60M2
STU9N60M2

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_{case} = 25 °C	5.5	A
	Drain current (continuous) at T_{case} = 100 °C	3.6	
I_{DM} (1)	Drain current (pulsed)	22	A
P_{TOT}	Total power dissipation at T_{case} = 25 °C	60	W
dv/dt (2)	Peak diode recovery voltage slope	15	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	°C
T_j	Operating junction temperature range		

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 5.5 A, di/dt ≤ 400 A/µs; $V_{DS\ peak}$ < $V_{(BR)DSS}$, V_{DD} = 400 V*
3. *V_{DS} ≤ 480 V*

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220	IPAK	
$R_{thj\text{-}case}$	Thermal resistance junction-case		2.08		°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	50			°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient		62.5	100	°C/W

1. *When mounted on 1 inch² FR-4, 2 Oz copper board*

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_{Jmax})	2	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	105	mJ

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 1 mA	600			V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V			1	µA
		V_{GS} = 0 V, V_{DS} = 600 V, T_{case} = 125 °C (1)			100	
I_{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 3 A		0.72	0.78	Ω

1. *Defined by design, not subject to production test.*

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	320	-	pF
C_{oss}	Output capacitance		-	18	-	
C_{rss}	Reverse transfer capacitance		-	0.68	-	
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	88	-	pF
R_G	Intrinsic gate resistance	f = 1 MHz, I_D = 0 A	-	6.5	-	Ω
Q_g	Total gate charge	V_{DD} = 480 V, I_D = 5.5 A, V_{GS} = 0 to 10 V (see Figure 16. Test circuit for gate charge behavior)	-	10	-	nC
Q_{gs}	Gate-source charge		-	2	-	
Q_{gd}	Gate-drain charge		-	5.1	-	

1. *$C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.*

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 300 V, I_D = 3 A, R_G = 4.7 Ω, V_{GS} = 10 V (see Figure 15. Test circuit for resistive load switching times and Figure 20. Switching time waveform)	-	8.8	-	ns
t_r	Rise time		-	7.5	-	
$t_{d(off)}$	Turn-off delay time		-	22	-	
t_f	Fall time		-	13.5	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		5.5	A
I_{SDM} (1)	Source-drain current (pulsed)		-		22	A
V_{SD} (2)	Forward on voltage	V_{GS} = 0 V, I_{SD} = 5.5 A	-		1.6	V
t_{rr}	Reverse recovery time	I_{SD} = 5.5 A, di/dt = 100 A/µs, V_{DD} = 60 V (see Figure 17. Test circuit for inductive load switching and diode recovery times)	-	265		ns
Q_{rr}	Reverse recovery charge		-	1.65		µC
I_{RRM}	Reverse recovery current		-	12.5		A
t_{rr}	Reverse recovery time	I_{SD} = 5.5 A, di/dt = 100 A/µs, V_{DD} = 60 V, T_j = 150 °C (see Figure 17. Test circuit for inductive load switching and diode recovery times)	-	377		ns
Q_{rr}	Reverse recovery charge		-	2.3		µC
I_{RRM}	Reverse recovery current		-	12.2		A

1. *Pulse width is limited by safe operating area.*
2. *Pulse test: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for DPAK and IPAK

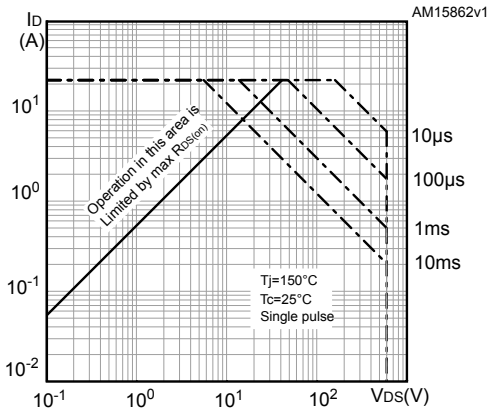


Figure 2. Thermal impedance for DPAK and IPAK

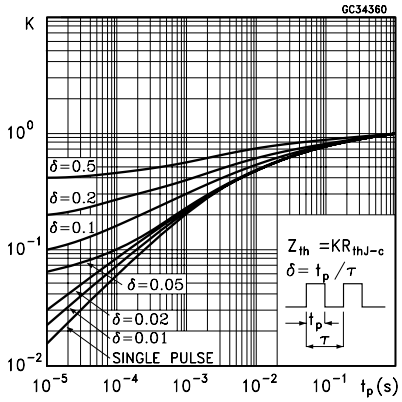


Figure 3. Safe operating area for TO-220

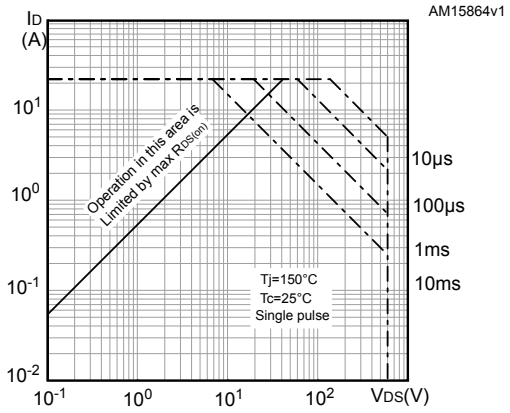


Figure 4. Thermal impedance for TO-220

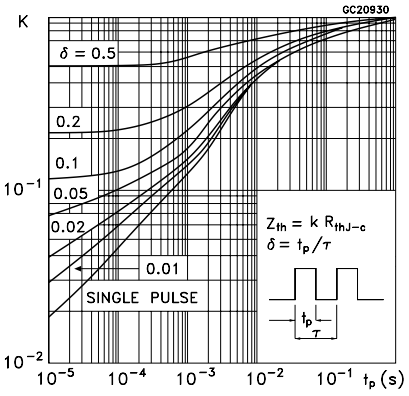


Figure 5. Output characteristics

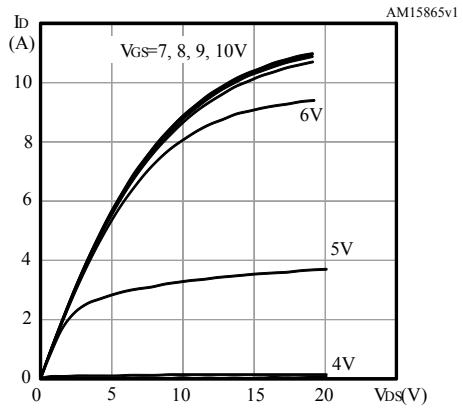


Figure 6. Transfer characteristics

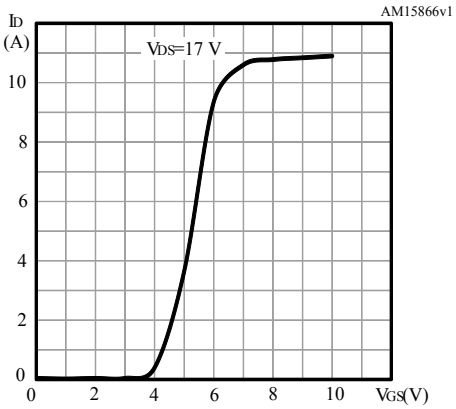


Figure 7. Gate charge vs gate-source voltage

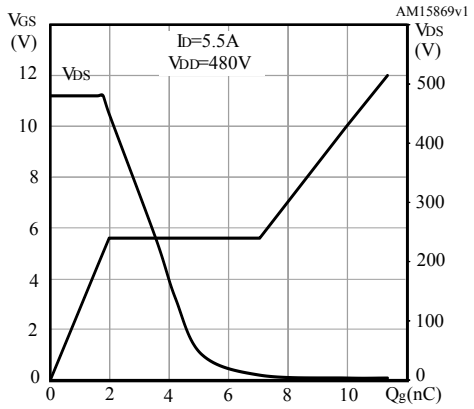


Figure 8. Static drain-source on-resistance

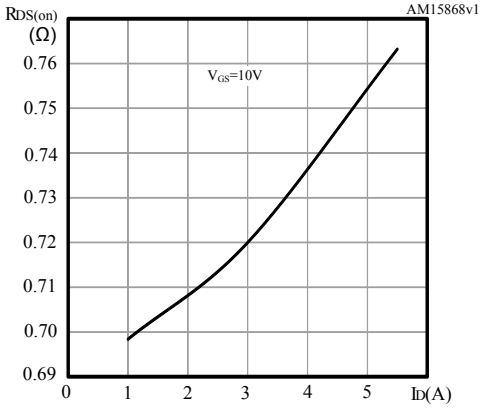


Figure 9. Capacitance variations

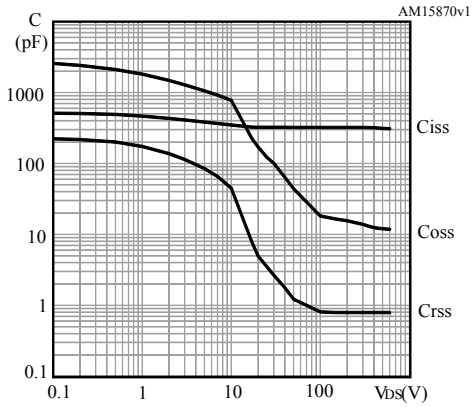


Figure 10. Output capacitance stored energy

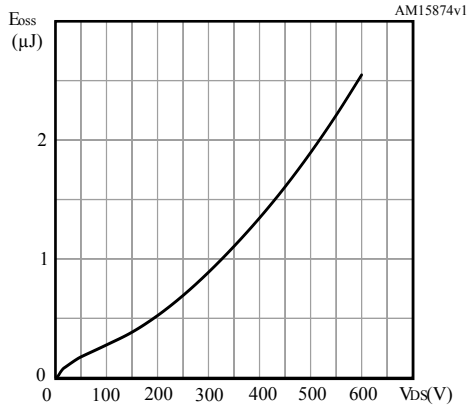


Figure 11. Normalized gate threshold voltage vs temperature

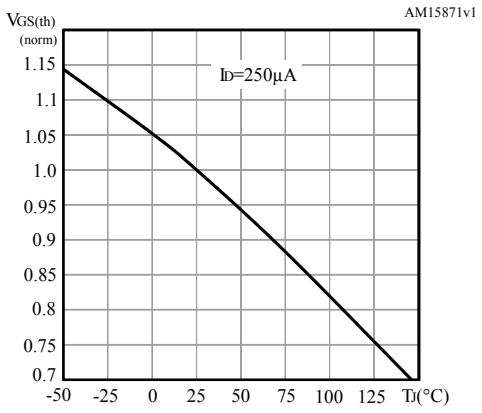


Figure 12. Normalized on-resistance vs temperature

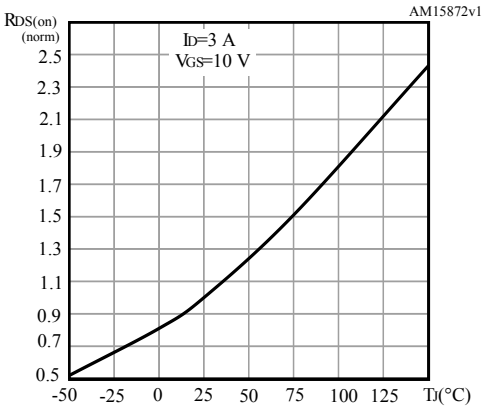


Figure 13. Source-drain diode forward characteristics

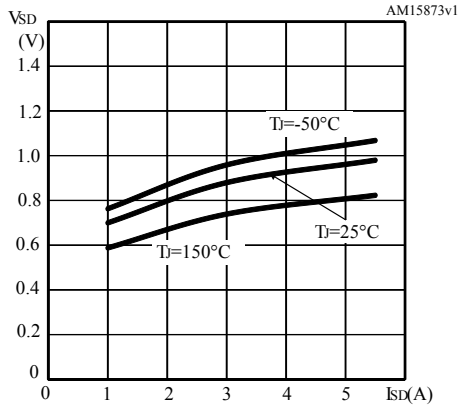
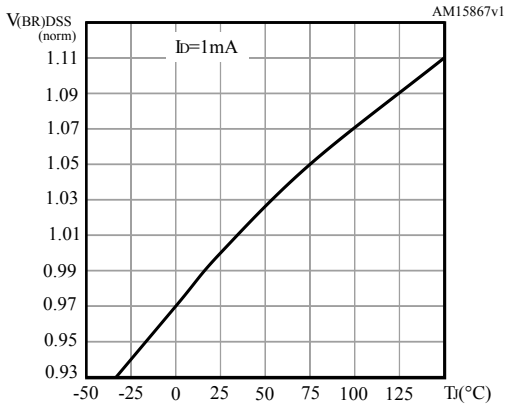


Figure 14. Normalized $V_{(BR)DSS}$ vs temperature



3 Test circuits

Figure 15. Test circuit for resistive load switching times

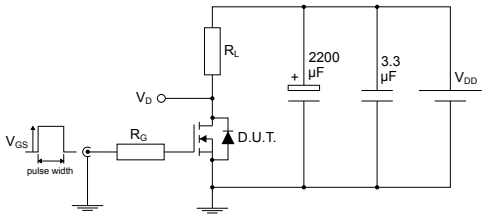


Figure 16. Test circuit for gate charge behavior

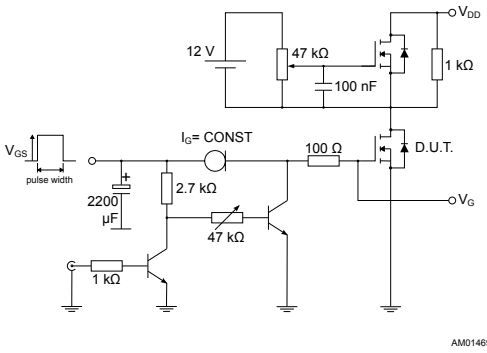


Figure 17. Test circuit for inductive load switching and diode recovery times

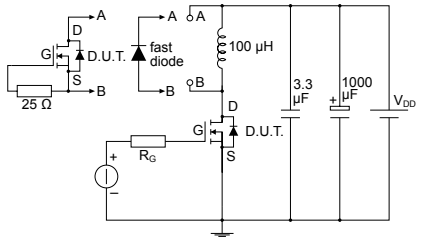


Figure 18. Unclamped inductive load test circuit

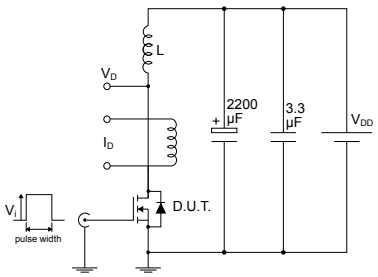


Figure 19. Unclamped inductive waveform

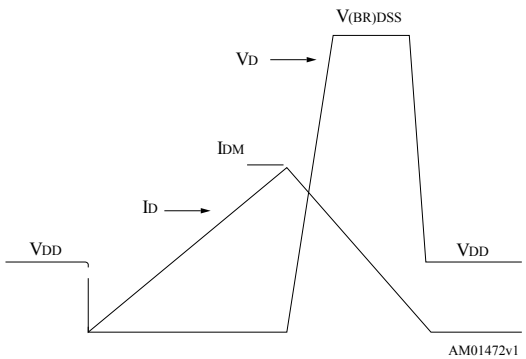
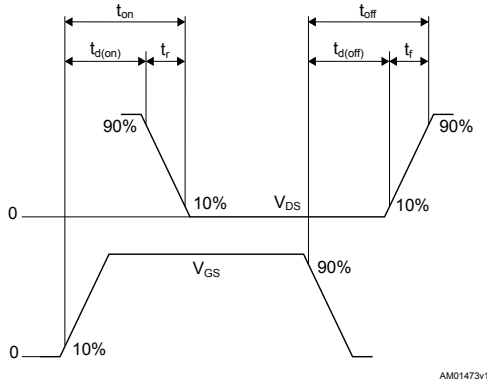


Figure 20. Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 21. **DPAK (TO-252) type A package outline**

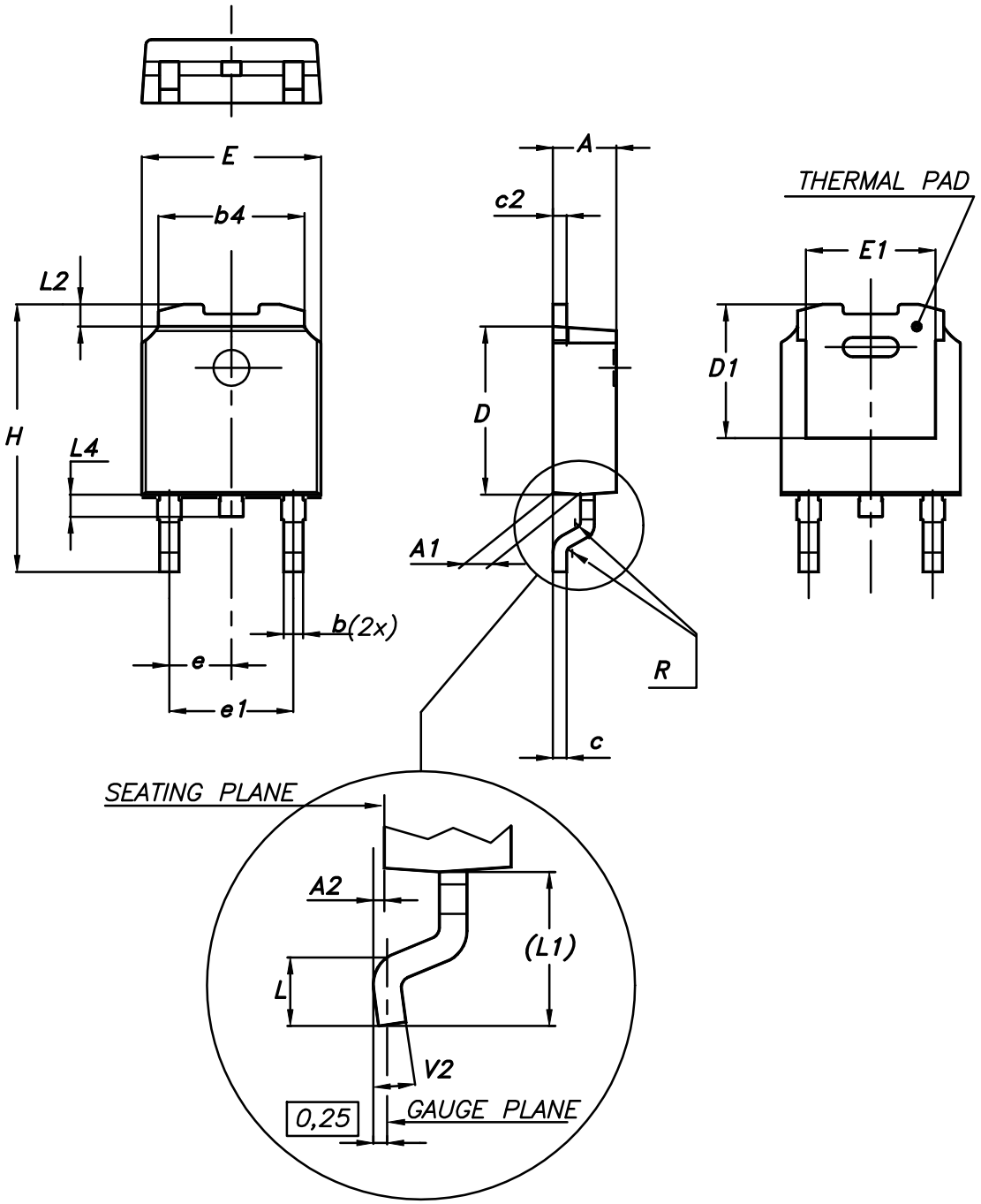


Table 8. **DPAK (TO-252) type A mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C package information

Figure 22. **DPAK (TO-252) type C package outline**

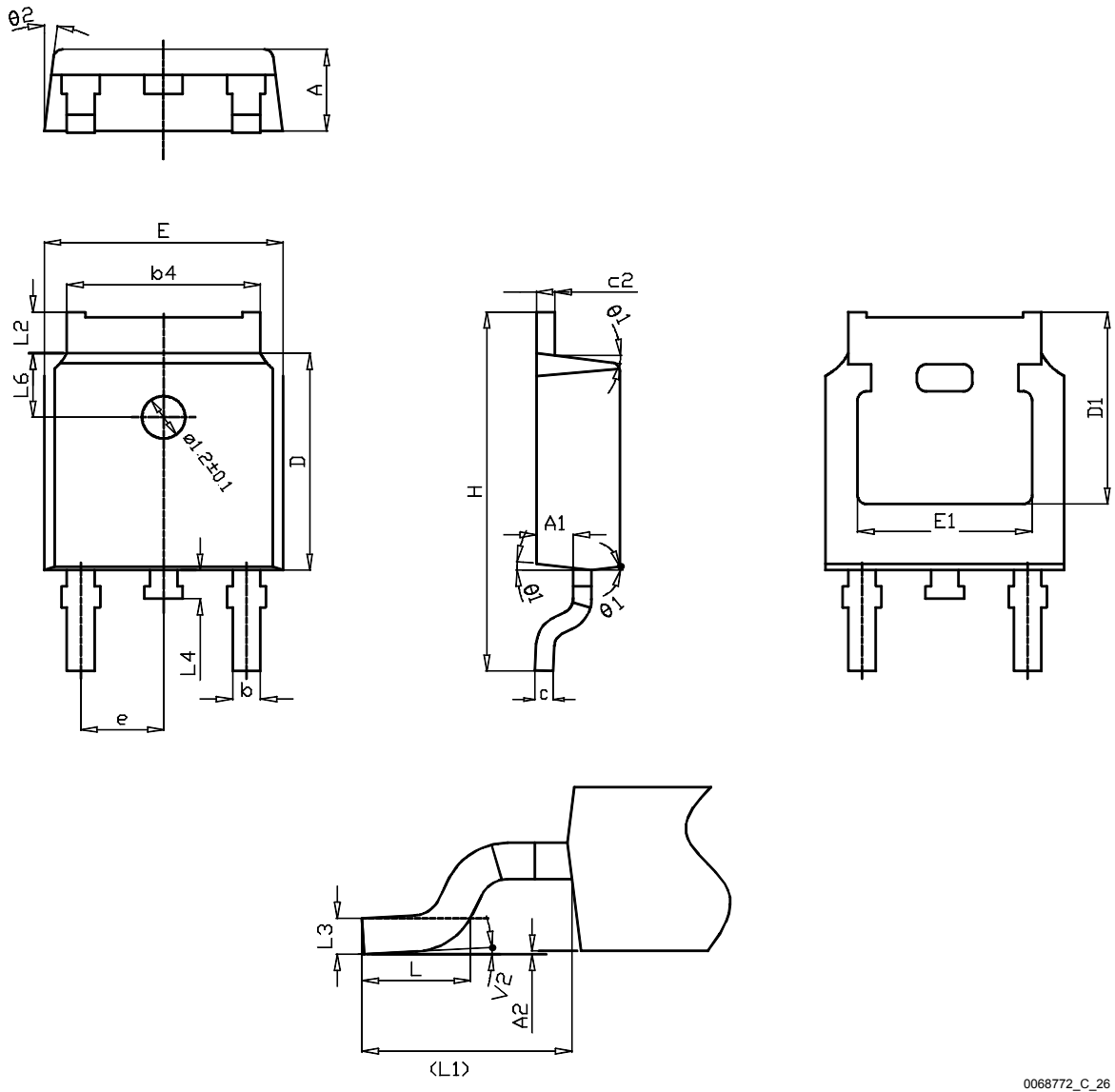


Table 9. **DPAK (TO-252) type C mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1		2.90 REF	
L2	0.90		1.25
L3		0.51 BSC	
L4	0.60	0.80	1.00
L6		1.80 BSC	
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

4.3 DPAK (TO-252) type E package information

Figure 23. **DPAK (TO-252) type E package outline**

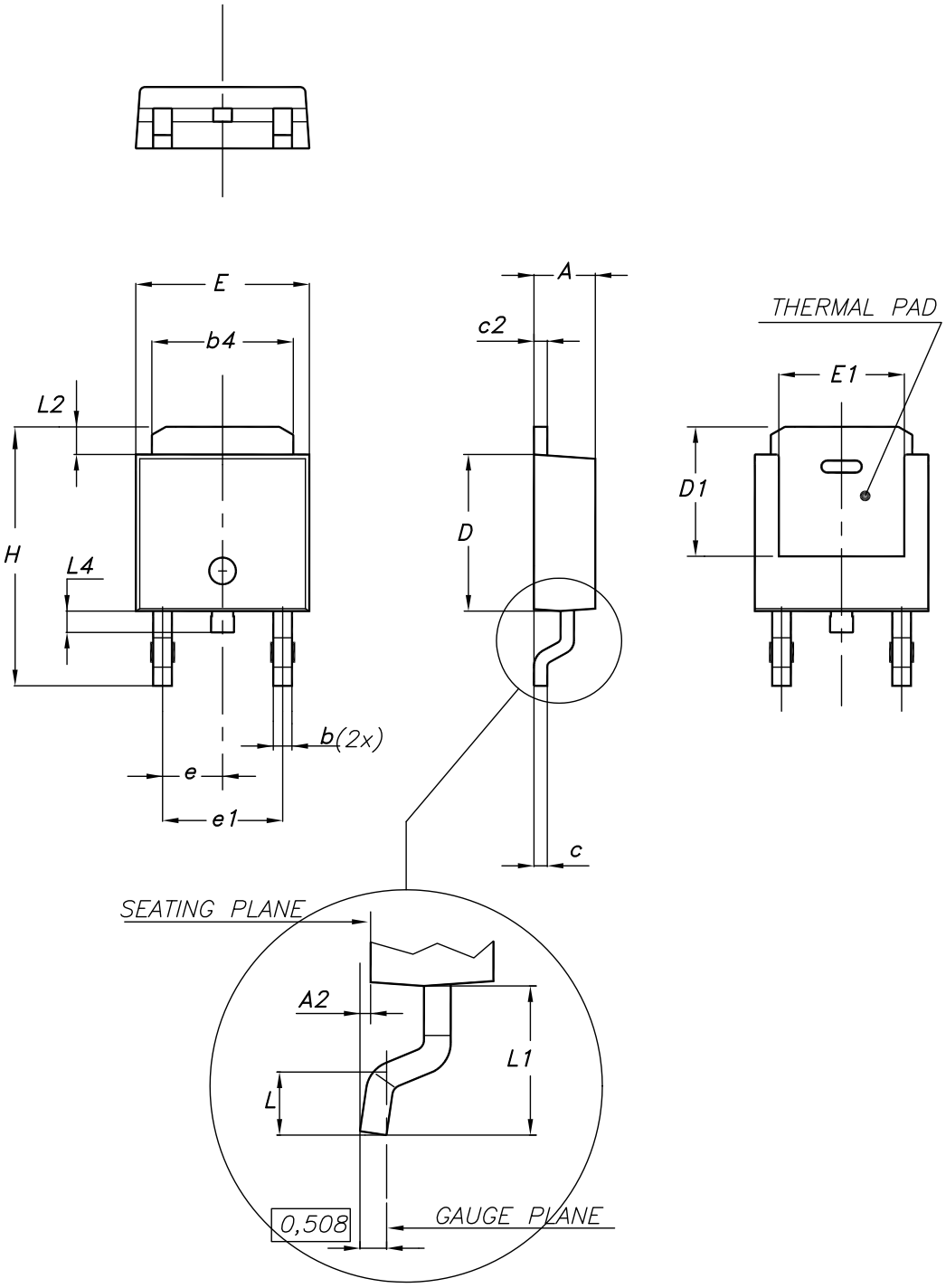
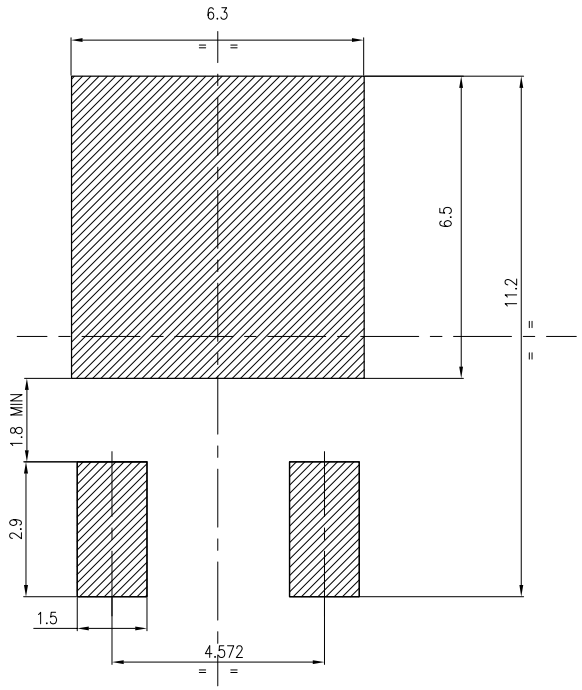


Table 10. **DPAK (TO-252) type E mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 24. **DPAK (TO-252) recommended footprint (dimensions are in mm)**



FP_0068772_26

4.4 DPAK (TO-252) packing information

Figure 25. **DPAK (TO-252) tape outline**

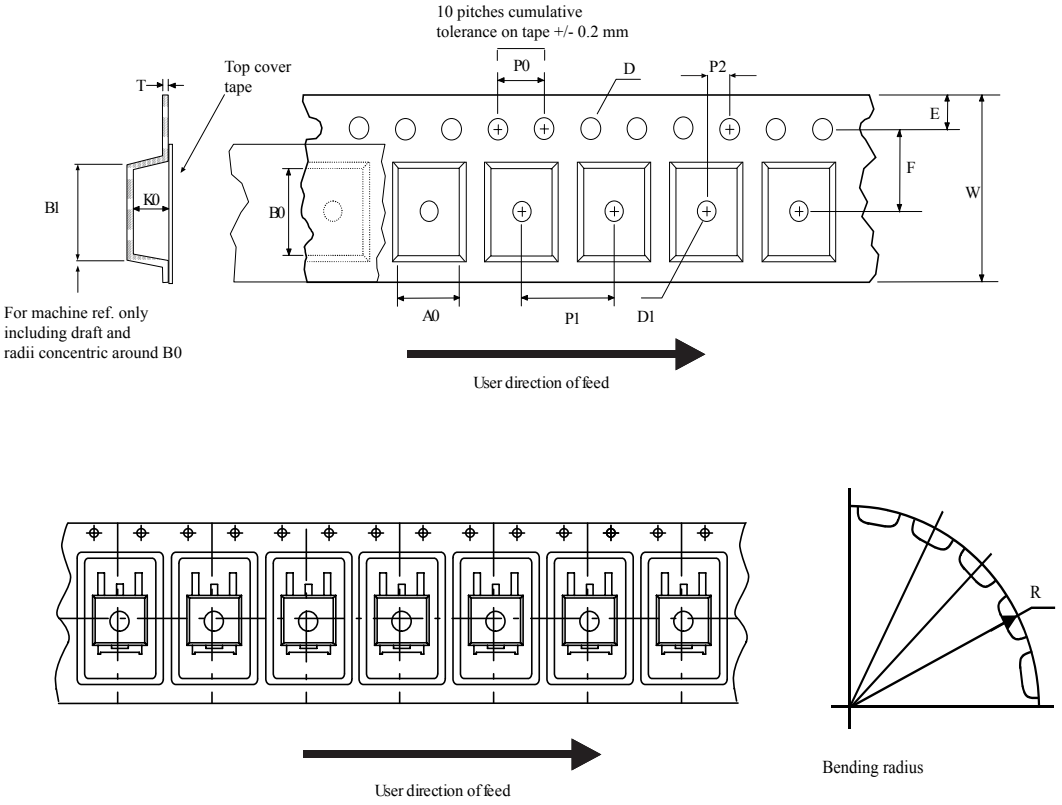
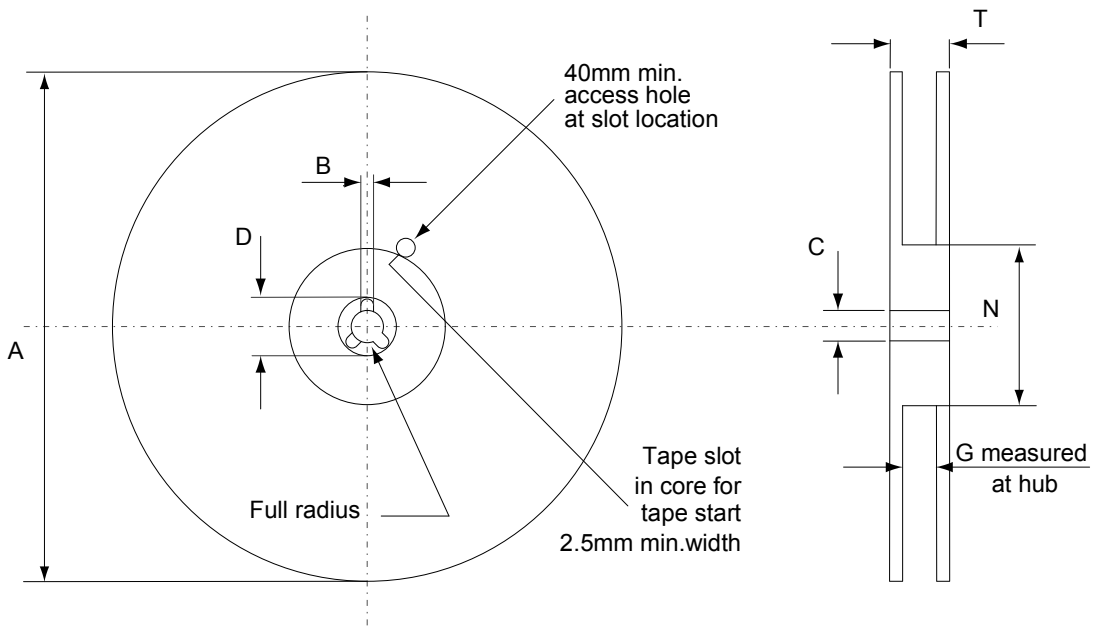


Figure 26. **DPAK (TO-252) reel outline**



AM06038v1

Table 11. **DPAK (TO-252) tape and reel mechanical data**

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.5 TO-220 type A package information

Figure 27. **TO-220 type A package outline**

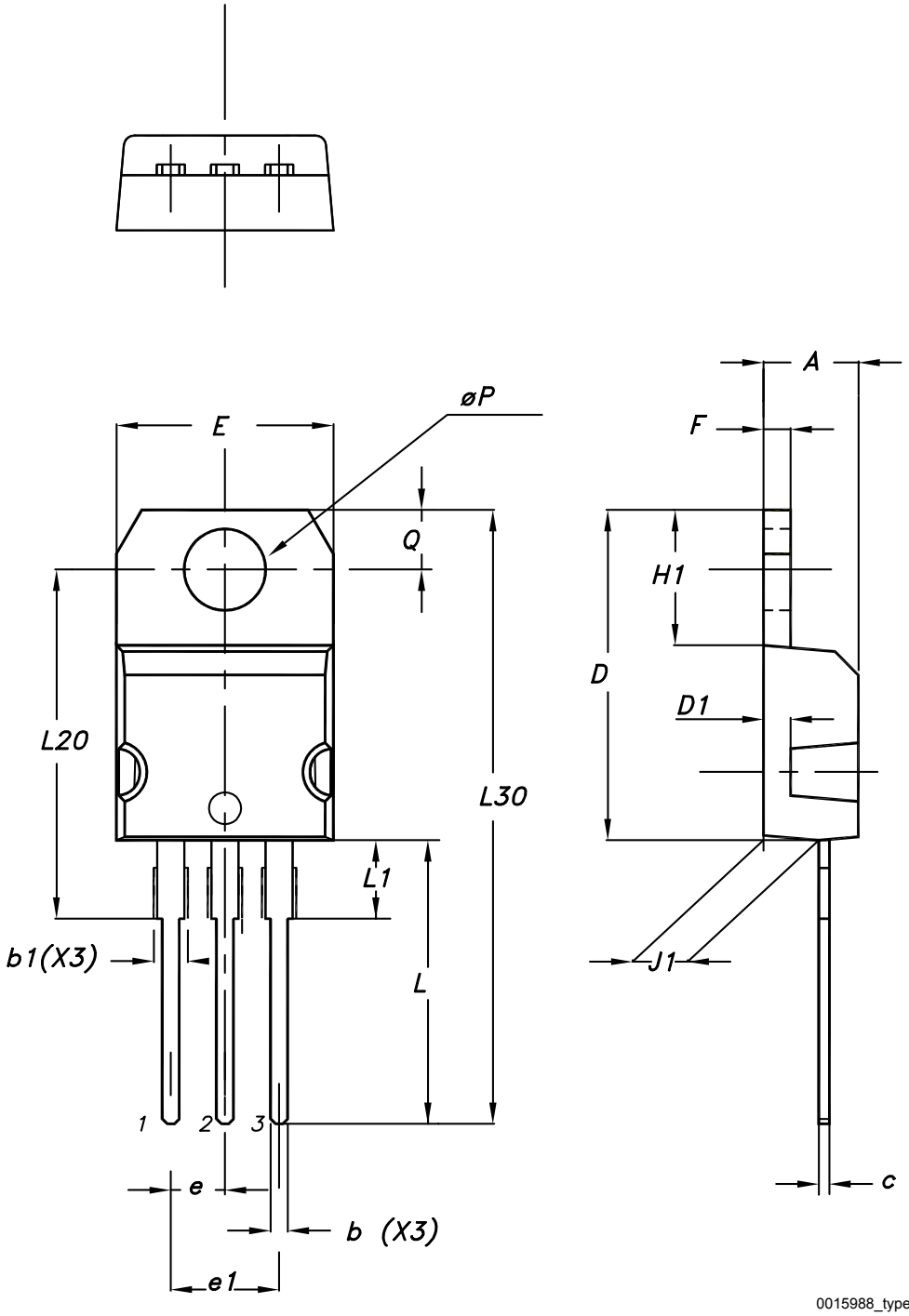


Table 12. **TO-220 type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.6 IPAK (TO-251) type A package information

Figure 28. **IPAK (TO-251) type A package outline**

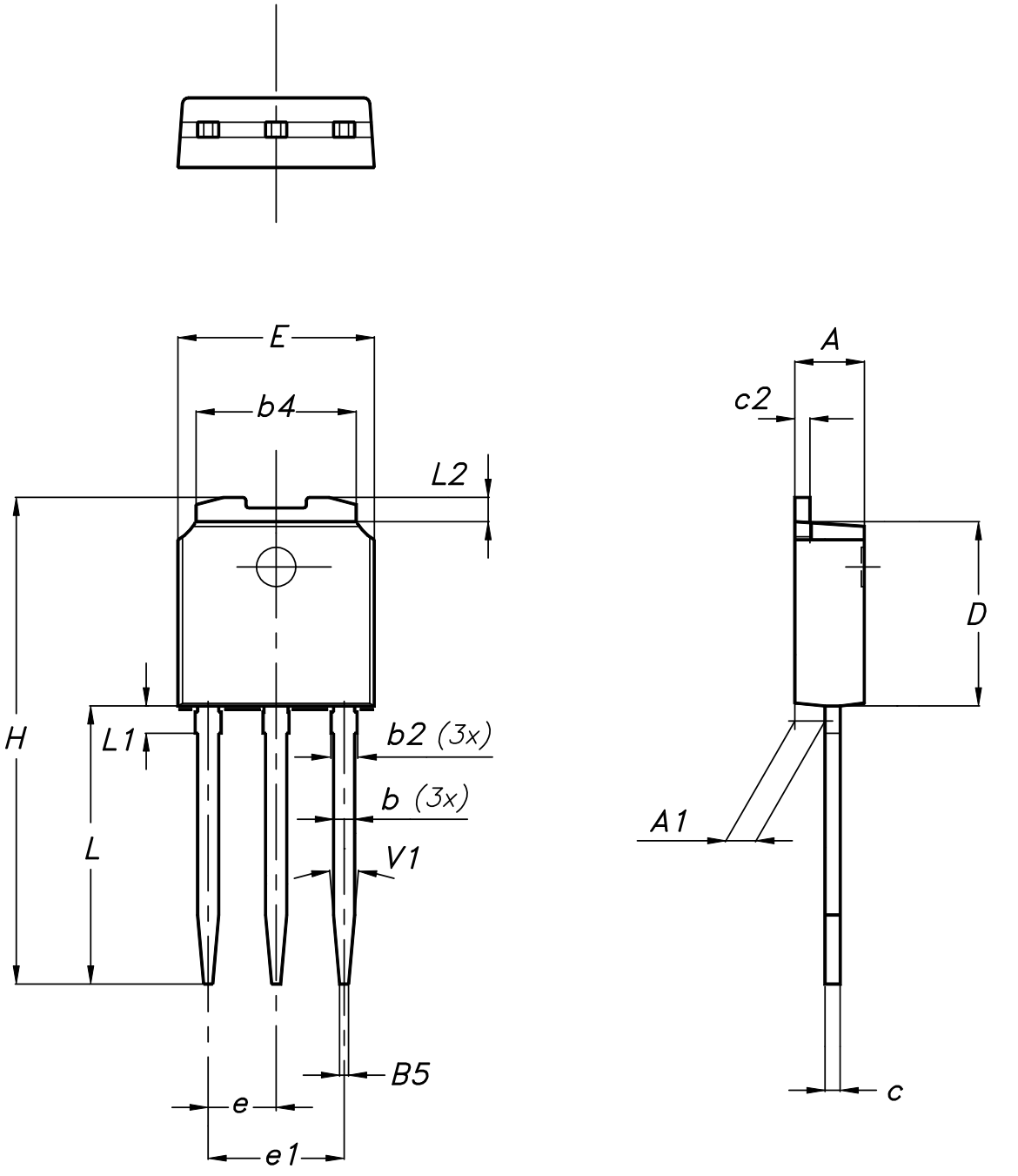
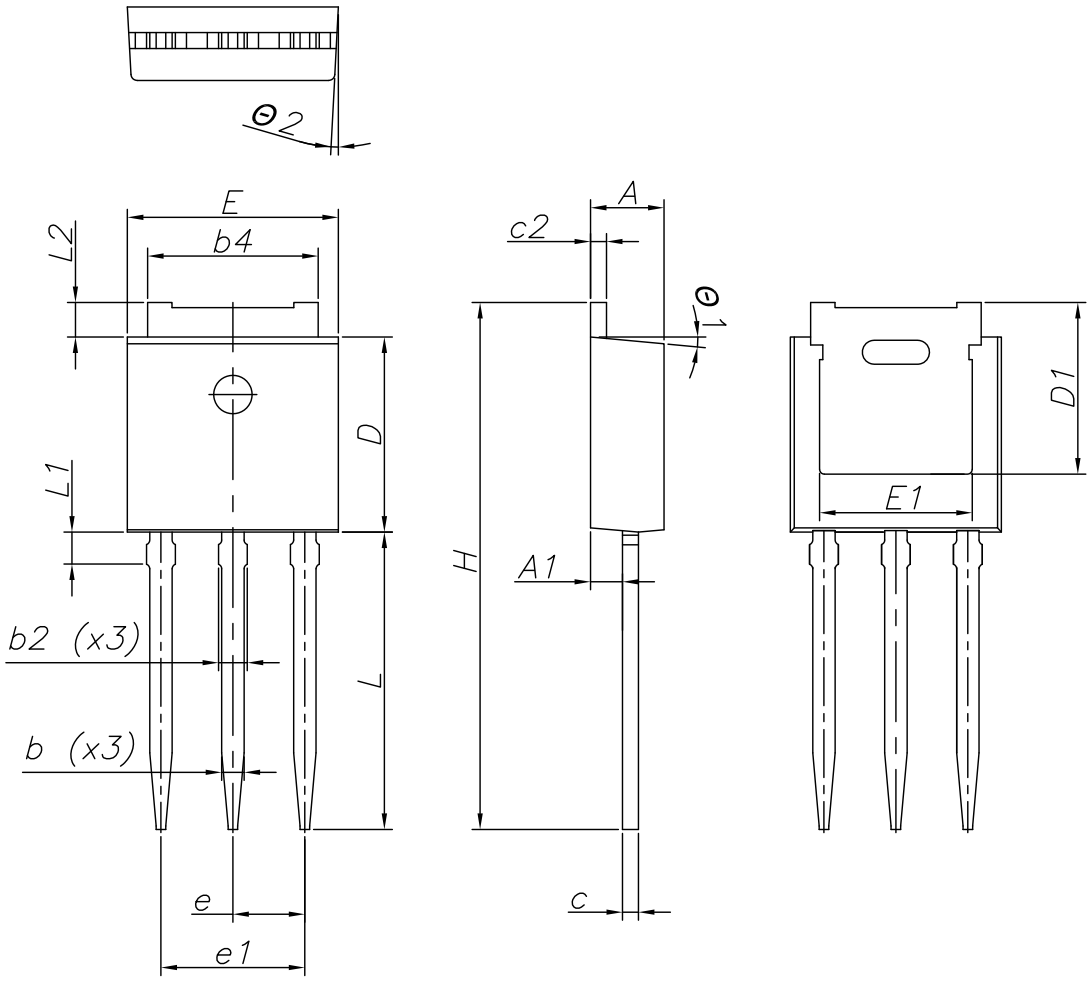


Table 13. **IPAK (TO-251) type A package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

4.7 IPAK (TO-251) type C package information

Figure 29. **IPAK (TO-251) type C package outline**



0068771_IK_typeC_rev14

Table 14. **IPAK (TO-251) type C package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

5 Ordering information

Table 15. **Order codes**

Order code	Marking	Package	Packing
STD9N60M2	9N60M2	DPAK	Tape and reel
STP9N60M2		TO-220	Tube
STU9N60M2		IPAK	

Revision history

Table 16. **Document revision history**

Date	Revision	Changes
19-Mar-2013	1	First release.
30-May-2013	2	– The part number STF9N60M2 has been moved to a separate datasheet. – Modified: I_{AR} and I_{AS} values, the entire typical values in *Table 4, 6, 7* and *8* – Updated: *Section 4: Package mechanical data* only for TO-220 package
12-Dec-2018	3	Removed maturity status indication from cover page. The document status is production data. Updated features and description on cover page. Modified Table 2. Thermal data. Added Section 4.2 DPAK (TO-252) type C package information, Section 4.3 DPAK (TO-252) type E package information and Section 4.6 IPAK (TO-251) type A package information. Minor text changes.

Contents

1 **Electrical ratings** 2
2 **Electrical characteristics** 3
2.1 Electrical characteristics (curves) 5
3 **Test circuits** 8
4 **Package information** 9
4.1 DPAK (TO-252) type A package information 9
4.2 DPAK (TO-252) type C package information 11
4.3 DPAK (TO-252) type E package information 13
4.4 DPAK (TO-252) packing information 15
4.5 TO-220 type A package information 17
4.6 IPAK (TO-251) type A package information 19
4.7 IPAK (TO-251) type C package information 21
5 **Ordering information** 24
Revision history 25

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics – All rights reserved